Silicon NPN Power Transistors 2SC2123

DESCRIPTION

·With TO-3 package
·Short switching times.
·High dielectric strength.

APPLICATIONS

·For use in TV horizontal deflection stage

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		12	A
P_T	Total power dissipation	T_C=25□	50	W
T_j	Junction temperature		175	□
T_{stg}	Storage temperature		-55~175	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA; I_B=0;	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0;	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=10A;I_B=2.5 A			3.3	V
V_{BEsat}	Base-emitter saturation voltage	I_C=10A;I_B=2.5 A			2.2	V
I_{CBO}	Collector cut-off current	V_{CB}=1000V;I_E=0			1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7V;I_C=0			1.0	mA
h_{FE}	DC current gain	I_C=8A ; V_{CE}=5V	5			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=10V		6		MHz

PACKAGE OUTLINE

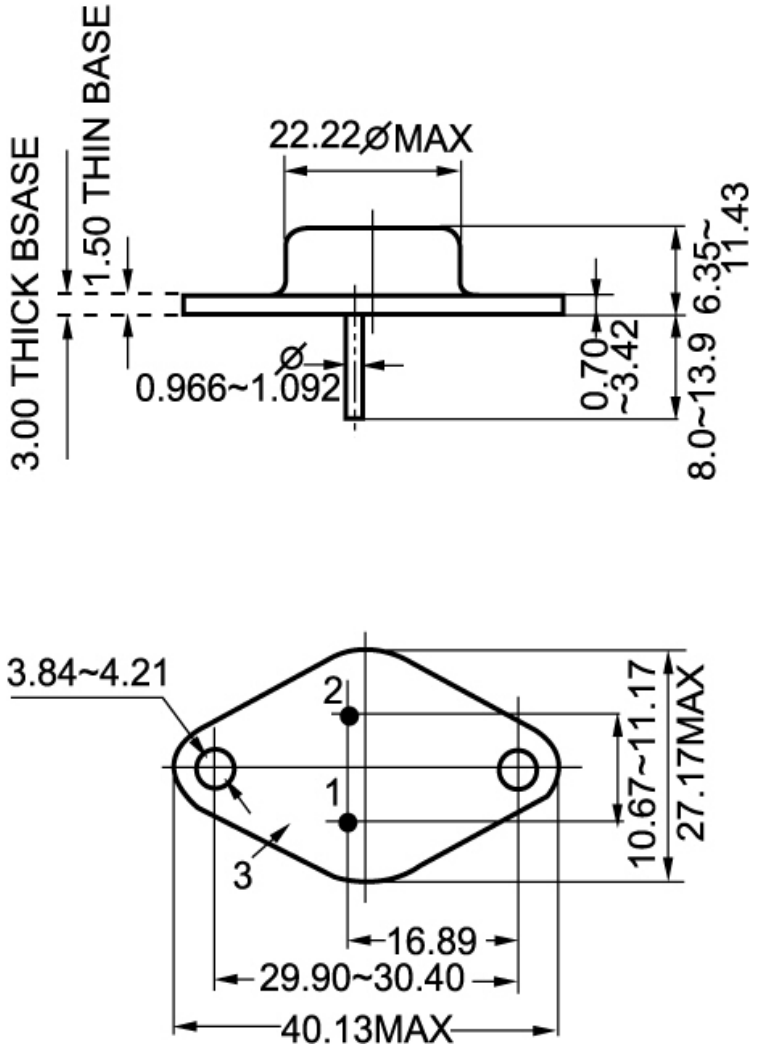

Fig.2 Outline dimensions